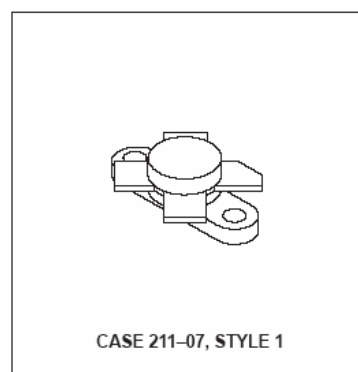
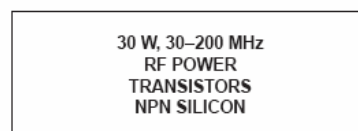


The RF Line NPN Silicon RF Power Transistors

... designed primarily for wideband large-signal driver and output amplifier stages in the 30–200 MHz frequency range.

- Guaranteed Performance at 150 MHz, 28 Vdc
Output Power = 30 Watts
Minimum Gain = 10 dB
- 100% Tested for Load Mismatch at All Phase Angles with 30:1 VSWR
- Gold Metallization System for High Reliability Applications



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CE0}	35	Vdc
Collector–Base Voltage	V_{CBO}	65	Vdc
Emitter–Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	3.4	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C	P_D	82 0.47	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	–65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.13	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 30 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	35	—	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 30 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	65	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 30 \text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	65	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 3.0 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	3.0	mAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 1.5 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	20	—	80	—
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NOTE:

1. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as RF amplifiers.

(continued)

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Output Capacitance ($V_{CB} = 30\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	—	30	40	pF
FUNCTIONAL TESTS (Figure 1)					
Common-Emitter Amplifier Power Gain ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 30\text{ W}$, $f = 150\text{ MHz}$)	G_{PE}	10	13.5	—	dB
Collector Efficiency ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 30\text{ W}$, $f = 150\text{ MHz}$)	η	50	—	—	%
Load Mismatch ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 30\text{ W}$, $f = 150\text{ MHz}$, VSWR = 30:1 all phase angles)	ψ	No Degradation in Power Output			

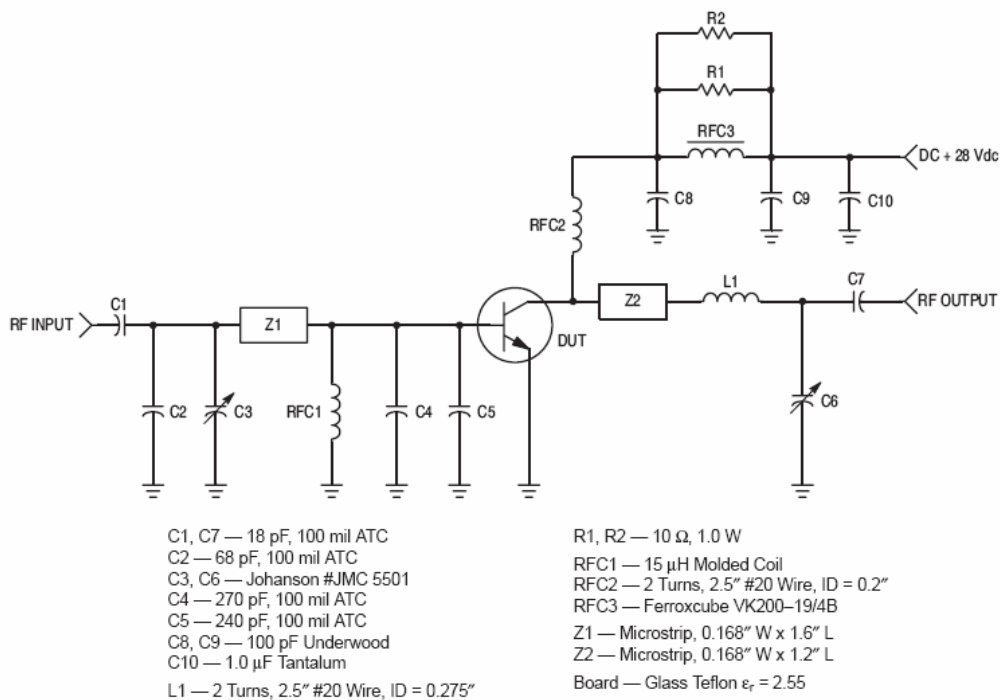


Figure 1. 150 MHz Test Circuit

TYPICAL PERFORMANCE CURVES

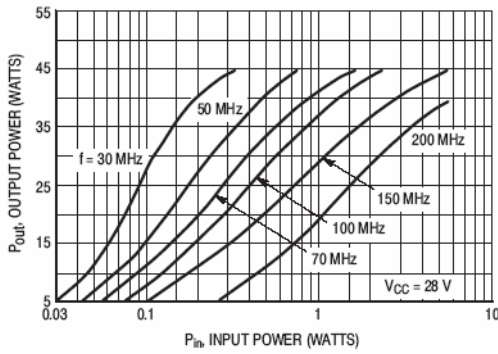


Figure 2. Output Power versus Input Power

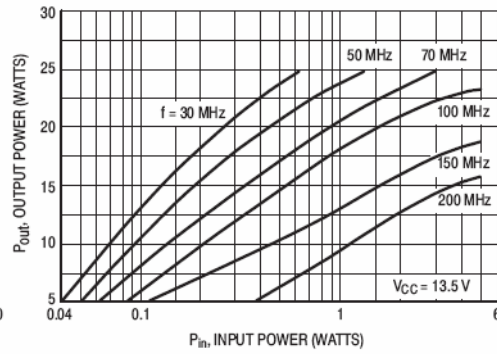


Figure 3. Output Power versus Input Power

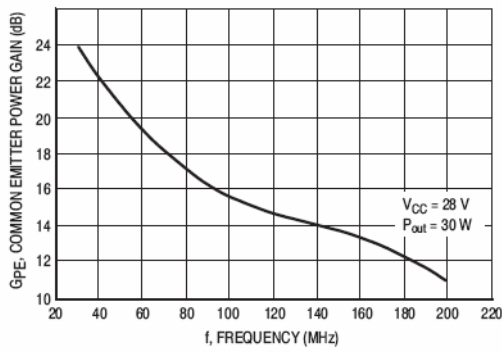


Figure 4. Power Gain versus Frequency

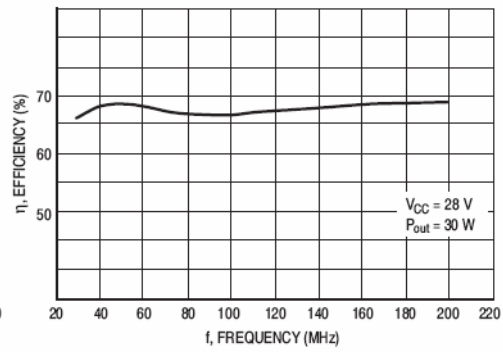


Figure 5. Efficiency versus Frequency

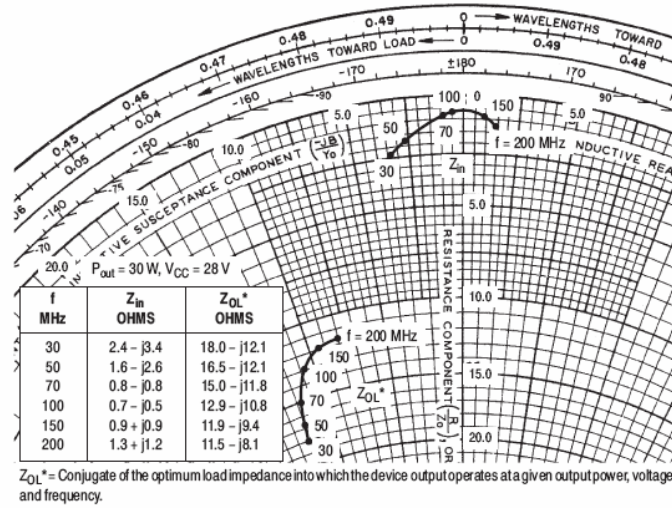
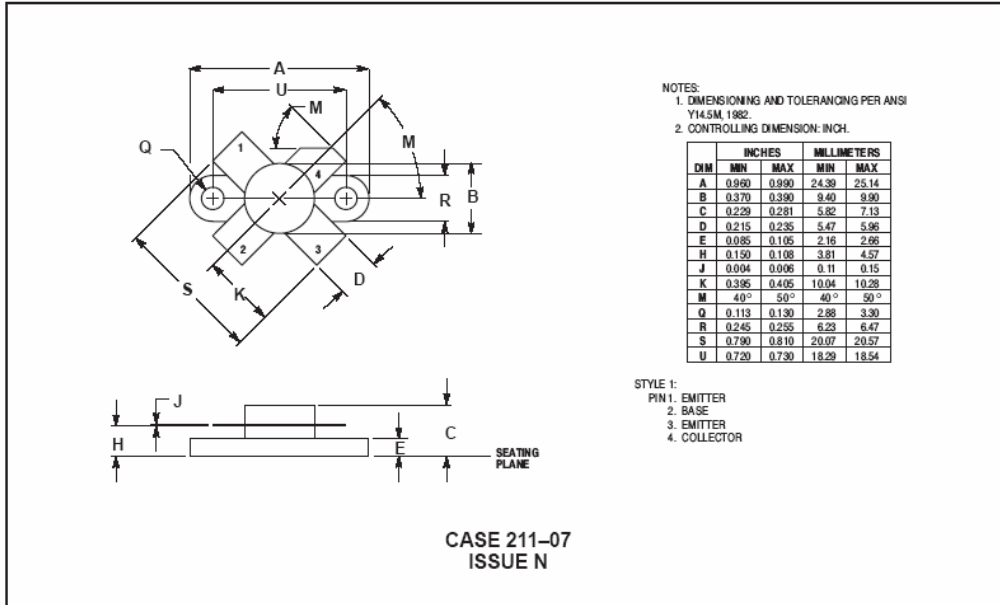


Figure 6. Series Equivalent Input/Output Impedance

PACKAGE DIMENSIONS





ELEFLOW OFFICES

<p>CHINA</p> <p>ELEFLOW TECHNOLOGIES(HQ) Suite1-603, HuaKang Plaza 109 ZhenXing Road, Futian District ShenZhen518031, P.R. China Phone: 86-755-83204665/83204663 Fax: 86-755-8320 4659 Email: eleflow@163.com</p> <p>USA</p> <p>ELEFLOW TECHNOLOGIES(USA) Mr. Ted Seymore (Manager) 3291 NE 4th Ave., Boca Raton Florida 33431-6011, USA Phone: 408-716-8509 Fax: 561-852-0505 Email: tedseymour@adelphia.net</p>	<p>R & D CENTER</p> <p>ELEFLOW TECHNOLOGIES(R&D CENTER) Overseas Chinese High-Tech Venture Park No. 12 South, Hi-tech Park, NanShan Dist. ShenZhen518057, China</p> <p>CHENGDU, CHINA</p> <p>Eleflow Technologies (Chengdu Office) Mr. Ou, Lin (Manager) Suite A401, Qunyi Business Centre 13 ErHuanLu NanYiDuan, Chengdu Sichuan610041, China Phone: 86-28-8521 3480 Fax: 86-28-8521 3480 Email: eleflow@163.com</p>
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